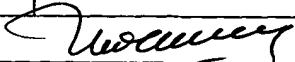


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U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
CVL	5,503,951	04/02/1996	Flanders et al.	430		04/17/1995	
CVL	5,565,286	10/15/1996	Lin	430		11/17/1994	
CVL	5,725,969	03/10/1998	Lee	430		12/22/1995	
CVL	6,004,702	12/21/1999	Lin	430		05/21/1998	
CVL	6,010,807	01/04/2000	Lin	430		04/07/1998	
CVL	4,890,309	12/26/1989	Smith, et al.	378	35	02/25/1987	
CVL	5,288,569	2/22/1994	Lin	430	5	4/23/1992	
CVL	6,312,854 B1	11/6/2001	Chen, et al.	430	5	3/16/1999	
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CVL	WO 98/38549	9/3/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
CVL	Wong, A., et al., "Deep UV Lithographic Approaches for 1Gh DRAM", 1997 Symposium on VLSI Technology Digest of Technical Papers, pp. 127-128 (1997).						
CVL	Chen, J. Fung, et al., "High-T, Ternary Attenuating PSFs for the 130nm Node", Microlithography World \, pp. 12, 14, 16, 18, 20 & 30 (2000).						
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		DATE CONSIDERED		5/24/06			

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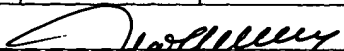
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CVL	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
CVL	4,456,371	6/26/84	Lin	355	71	6/30/82
CVL	4,812,962	3/14/89	Witt	364	490	4/9/87
CVL	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
CVL	5,051,598	9/24/91	Ashton, et al.	250	492.2	9/12/90
CVL	5,182,718	1/26/93	HaraFuji, et al.	364	490	3/29/90
CVL	5,241,185	8/31/93	Meiri, et al.	250	492.2	1/8/92
CVL	5,242,770	9/7/93	Chen, et al.	430	5	1/16/92
CVL	5,256,505	10/26/93	Chen, et al.	430	5	8/21/92
CVL	5,302,477	4/12/94	Dao, et al.	430	5	8/21/92
CVL	5,308,741	5/3/94	Kemp	430	312	7/31/92
CVL	5,316,878	5/31/94	Saito, et al.	430	5	6/4/92
CVL	5,328,807	7/12/94	Tanaka, et al.	430	311	6/7/91
CVL	5,340,700	8/23/94	Chen, et al.	430	312	11/3/93
CVL	5,352,550	10/4/94	Okamoto	430	5	4/23/93
CVL	5,364,716	11/15/94	Nakagawa, et al.	430	5	9/3/92
CVL	5,424,154	6/13/95	Borodovsky	430	5	12/10/93
CVL	5,447,810	9/5/95	Chen, et al.	430	5	2/9/94
CVL	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
CVL	5,523,186	6/4/96	Lin, et al.	430	5	12/16/94
CVL	5,532,090	7/2/96	Borodovsky	430	5	3/1/95
CVL	5,538,815	7/23/96	Oi, et al.	430	5	9/14/93
CVL	5,553,273	9/3/96	Liebmann	395	500	4/17/95
EXAMINER <i>Wadley</i>			DATE CONSIDERED 5/24/06			

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CVL	5,553,274	9/3/96	Liebmann	395	500	6/6/95
CVL	5,573,890	11/12/96	Spence	430	311	7/18/94
CVL	5,595,843	1/21/97	Dao	430	5	3/30/95
CVL	5,620,816	4/15/97	Dao	430	5	10/13/95
CVL	5,631,110	5/20/97	Shioiri, et al.	430	5	6/5/95
CVL	5,635,316	6/3/97	Dao	430	5	10/13/95
CVL	5,636,002	6/3/97	Garofalo	355	53	10/31/95
CVL	5,657,235	8/12/97	Liebmann, et al.	364	474.24	5/3/95
CVL	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95
CVL	5,663,893	9/2/97	Wampler, et al.	364	491	5/3/95
CVL	5,702,848	12/30/97	Spence	430	5	8/23/96
CVL	5,705,301	1/6/98	Garza, et al.	430	5	2/27/96
CVL	5,707,765	1/13/98	Chen	430	5	5/28/96
CVL	5,723,233	3/3/98	Garza, et al.	430	5	2/27/96
CVL	5,740,068	4/14/98	Liebmann, et al.	364	489	5/30/96
CVL	5,761,075	6/2/98	Oi, et al.	364	488	5/31/96
CVL	5,766,804	6/16/98	Spence	430	5	8/23/96
CVL	5,766,806	6/16/98	Spence	430	5	9/9/96
CVL	5,807,649	9/15/98	Liebmann, et al.	430	5	10/31/96
CVL	5,815,685	9/29/98	Kamon	395	500	9/15/95
CVL	5,821,014	10/13/98	Chen, et al.	430	5	2/28/97
CVL	5,825,647	10/20/98	Tsudaka	364	167.03	3/12/96
CVL	5,827,623	10/27/98	Ishida, et al.	430	5	10/30/96
CVL	5,847,959	12/8/98	Veneklasen, et al.	364	468.28	1/28/97
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CVL	5,858,580	1/12/99	Wang, et al.	430	5	9/17/97
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CVL	5,879,844	3/9/99	Yamamoto, et al.	430	30	12/20/96
CVL	5,885,734	3/23/99	Pierrat, et al.	430	5	8/15/96
CVL	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97
CVL	5,923,566	6/13/99	Galan, et al.	364	489	3/25/97
CVL	5,994,002	11/30/99	Matsuoka	430	5	9/4/97
CVL	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99
CVL	6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97
CVL	6,081,658	6/27/00	Rieger, et al.	395	500.22	12/31/97
CVL	6,083,275	7/4/00	Heng, et al.	716	19	1/9/98
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	APPLICANT Pierrat, et al.	
	FILING DATE 9/9/2003	GROUP unknown
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	Aekmann, P. et al., "Phase Shifting And Optical Proximity Corrections To Improve CD Control On Logic Devices In Manufacturing For Sub 0.35 μm 1-Line", <i>Advance Micro Devices</i> (8 pages).	
	Asai, S. et al., "High Performance Optical Lithography Using A Separated Light Source", <i>J. Vac. Sci. Technol. B</i>, Vol. 10, No. 6, pp. 3023-3026, November/December 1992.	
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EXAMINER 	DATE CONSIDERED	

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	APPLICANT Pierrat, et al.	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	Fukuda, H. et al., "Determination Of High-Order Lens Aberration Using Phase/Amplitude Linear Algebra", <i>J. Vac. Sci. Technol. B</i>, Vol. 17, No. 6, pp. 3318-3321, November/December 1999.	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	Inokuchi, K. et al., "Sub-Quarter-Micron Gate Fabrication Process Using Phase-Shifting Mask For Microwave GaAs Devices", <i>Japanese Journal of Applied Physics</i> , Vol. 30, No. 12B, pp. 3818-3821, December 1991.	
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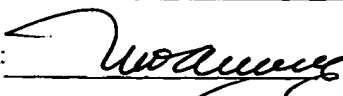
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			Applicant PIERRAT, Christophe		Group unknown	
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